

"METHOD FOR FABRICATION OF FIELD-EFFECT TRANSISTOR TO REDUCE
DEFECTS AT MOS INTERFACES FORMED AT LOW TEMPERATURE"

IN THE CLAIMS

Claims 2-6 and 9-14 are provided below in clean form in order to overcome objections by the Examiner. Applicant includes herewith an Attachment for Claim Amendments showing a marked up version of each amended claim.

2. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein heat treatment of said gate insulating film is conducted at a temperature of no less than 100°C.

AI 3. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein the formation of said gate insulating film is conducted while heating of said substrate is being prohibited.

4. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein the formation of said gate insulating film is conducted while said substrate is being cooled to a temperature of no higher than room temperature.

5. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein said gate insulating film is formed by a plasma CVD method.

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end

6. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein said gate insulating film is formed by a microwave plasma CVD method.

9. (Amended) The method for the fabrication of a field-effect transistor according to claim 8, wherein heat treating of said gate insulating film is conducted at a temperature of no less than 100°C.

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10. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film is conducted while heating of said substrate is being prohibited.

11. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film is conducted while said substrate is being cooled to a temperature of no higher than room temperature.

12. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film is conducted by a plasma CVD method.

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13. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film is conducted by a microwave plasma CVD method.

14. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said second-stage insulating film is conducted by a plasma CVD method using TEOS gas.

REMARKS

Claims 1-16 are now pending in the application. The Examiner is respectfully requested to reconsider and withdraw the rejection in view of the remarks contained herein.

CLAIM OBJECTIONS

Claims 2-6 and 9-14 are objected to because there are too many spaces in between the words "film is conducted" in claims 2-4 and 9-14 and "film is formed" in claims 5-6. Also, in claim 9, the degree symbol should have been a superscript.

Claims 2-6 and 9-14 have been amended to overcome these deficiencies. Therefore, reconsideration and withdrawal of the objections is respectfully requested.